

*AB*  
of3 form potentials shown by the curve b of Fig. 6. The potential on the side of the semiconductor substrate 11 hardly changes because the electric potential applied to the semiconductor substrate 11 is not altered between the first and second image pickup operations.

On page 64, delete the Abstract Of The Disclosure set forth therein and substitute the following new Abstract.

### ABSTRACT OF THE DISCLOSURE

*AB*  
A solid-state image pickup device for generating image signals in accordance with incident light includes a semiconductor substrate with a semiconductor region formed on one surface thereof, plural channel regions extending in a column direction on the region and defining plural picture elements in which electric charges are accumulated, and plural transfer electrodes extending in a row direction on the semiconductor region. The picture elements include light receiving elements accumulating electric charges according to incident light and storage elements for storing charges transferred from the light receiving elements. The light receiving elements include a first set in which corresponding transfer elements are simultaneously activated and inactivated in first and second image pickup operations and a second set in which all corresponding transfer electrodes are inactivated in the first image pickup operation and transfer electrodes are simultaneously activated and inactivated in the second image pickup operation.

### IN THE CLAIMS:

Rewrite claim 1 as follows:

- Sub 2*  
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1. (Amended) A solid-state image pickup device for generating image signals in accordance with incident light, comprising:  
a semiconductor substrate having one conductive type;  
a semiconductor region formed on one surface of said semiconductor substrate and having a conductive type opposite to said semiconductor substrate;